

Effects of extended Stone-Wales defects on the electronic structure of graphene nanotubes: an ab-initio real space recursion approach.

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In this communication we propose an ab-initio combination of the Linear Muffin tin Orbital and the Recursion Method to study the effect of extended Stone-Wales defects in graphene nanotubes. We have successfully applied this to zigzag and armchair tubes. The results contain no intrinsic mean-field like assumptions or external parameter fitting. As defects proliferate, the low density of states near the Fermi levels of the pristine tubes are filled with defect states. The increase of DOS at the Fermi level leads to enhanced conduction.

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I. INTRODUCTION

From the way graphene is prepared it is quite plausible that disorder is ubiquitous in it. Defect based nano-engineering of graphenic structures have always focused on tubular forms¹⁻³ in addition to sheets. Not only local defects like adatoms or vacancies but also extended defects like Stone-Wales⁴ or patches of other allotropes in a pristine graphene background have been studied⁵⁻¹³.

First principle studies of extended defects have been beyond the scope of mean-field approaches. The most successful among these, the coherent potential approximation (CPA) can study only very local disorder. The alternative

supercell approaches always lead to sharp bands, or the singularities of the spectral function are always real. This is because on some length scale (size of the super-cell) lattice translation symmetry and Bloch's Theorem still hold. Any estimate of disorder related life-times or band broadening requires smoothening with external parameters. In that sense the approach is not fully ab-initio. However, the purely real space based recursion method, proposed by the Cambridge group¹⁵, appears to be ideally suited for the study of such extended defects. It is surprising that its use has been rather limited in this particular area of study. We shall present here a recursion based study of such defects and their influence on the electronic structure of graphene nano-tubes. . The recursion method¹⁴⁻¹⁶ intro-

duced by Heine and co-workers is a powerful alternative to the Bloch theorem based techniques and comes to its own when Bloch theorem is violated. A large body of work exist using the recursion method on the study of systems like plane and rough surfaces^{18–21} and interfaces¹⁴, defects and dopants, disordered alloys¹⁷, amorphous networks^{22,23} and frustrated spin systems²⁴.

A. Nanotube and Stone-Wales Defects

The left panel (a) in Fig.1 shows a pristine two-dimensional honeycomb structure. If we fold this about x-axis then we obtain a zigzag type nanotube (Fig.1 middle panel (b)). Whereas folding about y-axis leads to a nanotube of the armchair type^{7,25–31} (Fig.1 right panel (c)). A general identification of the type of nanotube is given by chiral vectors. A zigzag type nanotube is described by $(n, 0)$ and armchair type by (n, n) . Fig.1(b) is a $(6, 0)$ and Fig.1(c) is a $(3, 3)$ nanotube. Electronic properties of these two types have been investigated by other techniques before and accordingly zigzag type nanotubes are called semiconductor nanotubes and armchair types are known as metallic nanotubes^{25,27,32}. We studied the electronic properties of these two types with and without Stone-Wales (S-W) defects.

Stone-Wales (S-W) defects^{33–47} are pure geometrical extended defects which occur due to rotation of two neighbouring atoms shown in red in Fig.2, followed by rebonding of the dangling bonds so produced.. A single S-W defect spreads over sixteen atoms and transforms four adjacent hexagonal cells into two pentagonal and two heptagonal cells shown in green in Fig.2(a). In a double S-W defect, twenty four atoms are involved and six adjacent hexagonal cells transform into one rhombic, two pentagonal and four heptagonal cells shown in green in Fig.2(b).

II. METHODOLOGY

The elements of the representation of the tight binding Anderson Hamiltonian⁵³ have been obtained first from an ab-initio, self-consistent, tight-binding linear muffin-tin orbitals technique (TB-LMTO)^{48–50}. The resulting Hamiltonian basis is multi-orbital with s, p and d elements.

Our interest is in the p_z sector only. We then use the N-th order muffin-tin orbital (NMTTO method)^{51,52} and massively downfold to obtain the p_z Hamiltonian.

(eV)	ε	t
	-0.291	-2.544

The NMTTO Hamiltonian for the p_z sector of C

$$\hat{H} = \sum_i \varepsilon_i |i\rangle\langle i| + \sum_{\{i,j\}} t_{ij} \{|i\rangle\langle j| + |j\rangle\langle i|\} \quad (1)$$

where the site labelled basis $\{i\}$ is used for representation, $\{i, j\}$ refer to nearest neighbour pairs in the material and $\langle i|j\rangle = \delta_{ij}$.

The recursion transformation of basis from $\{|i\rangle\}$ to $\{|u_n\rangle\}$, which converts the tight-binding Hamiltonian into a Jacobian matrix has been described in great detail by Haydock *et.al.*^{14–16}. Note that there is absolutely no symmetry restriction on the matrix : no translation symmetry or local geometric symmetries. It is enough that the basis is denumerable. The recursion method does not necessarily invoke the Bloch Theorem and therein lies its strength.

$$\begin{aligned} |u_1\rangle &= |k\rangle \quad (\text{our choice}) \\ |u_{n+1}\rangle &= \hat{H}|u_n\rangle - \alpha_n|u_n\rangle - \beta_n^2|u_{n-1}\rangle \end{aligned} \quad (2)$$

$$\begin{aligned} \alpha_n &= \langle u_n|\hat{H}|u_n\rangle / \langle u_n|u_n\rangle \\ \beta_{n+1}^2 &= \langle u_{n+1}|u_{n+1}\rangle / \langle u_n|u_n\rangle \end{aligned} \quad (3)$$

Now, the diagonal element of Green's function in matrix representation given as :

$$\begin{aligned} G_{nn}(z) &= \langle u_n | \left(z\hat{I} - \hat{H} \right)^{-1} | u_n \rangle \\ &= \frac{1}{z - \alpha_1 - \frac{\beta_1^2}{z - \alpha_2 - \frac{\beta_2^2}{\ddots z - \alpha_N - T(z)}}} \end{aligned} \quad (4)$$

The terminator $T(z)$ is built up from the asymptotic behaviour of initial coefficients together with the known singular points in the

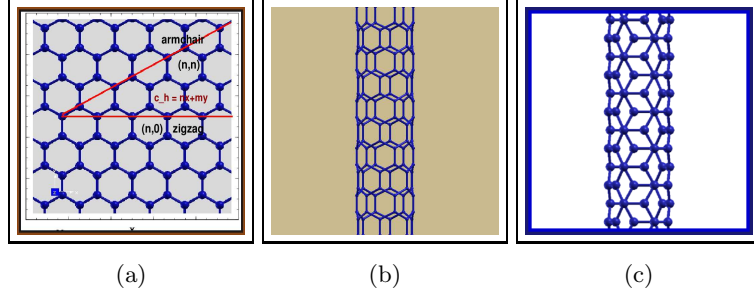


FIG. 1. (a) An ordered graphene lattice ; (b) a zigzag nanotube; (c) an armchair nanotube

The local density of states (LDOS) and total density of states (TDOS) are defined as

$$\begin{aligned} n_0(E) &= -(1/\pi) \lim_{\delta \rightarrow 0} \Im G_{00}(z) \\ n(E) &= -(1/\pi) \lim_{\delta \rightarrow 0} \Im \text{Tr} G(z) \end{aligned} \quad (5)$$

Numerically, we can not iterate the continued fraction for infinite number of steps, so, we must terminate this continued fraction at some stage. A good description of terminators is given by Muller and Viswanath⁵⁴. The manner in which the coefficients behave as $n \rightarrow \infty$ reflects upon the band widths and integrable singularities on the compact spectrum

We have used terminators of type given as

$$T(z) = \frac{2\pi}{E_0^4} |E| (E_0^2 - E^2) \quad (6)$$

with expansion coefficients

$$\beta_{2n}^2 = \frac{E_0^2 n}{2(2n+1)} \quad \beta_{2n+1}^2 = \frac{E_0^2 (n+2)}{2(2n+3)}$$

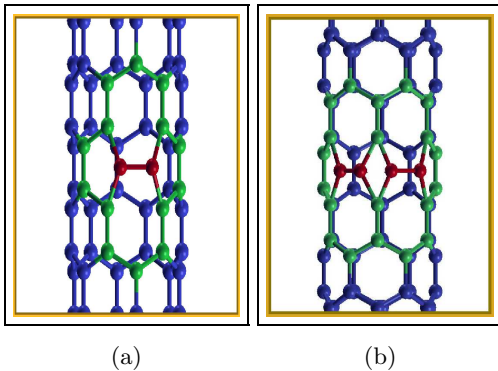


FIG. 2. (a) Single and (b) Double Stone-Wales defects in a zigzag type nanotube.

where $\pm E_0$ are the band edges. Using terminators the $\{\alpha_n\}$ and $\{\beta_n\}$ are plotted against n in Fig.3 for some cases.

III. RESULTS AND DISCUSSIONS

This section is divided in two parts: in the first we present a discussion on how the calculated values of Hamiltonian parameters ϵ and t obtained by the tight binding linear muffin tin orbitals method (TB-LMTO/NMTO) reproduce results in case of nanotubes with defects. In the second we present a comparative discussion between the LDOS for zigzag type and armchair type nanotubes with S-W defects.

In earlier works the energy was usually expressed in terms of $(E - \epsilon)/E_b$ where $E_b = 2Zt$ is the bandwidth and Z is the number of nearest neighbours of each atom. So, they chose $\epsilon = 0$ and $t = 1$. However when defects are introduced α_n varies with n and this shift of the origin to a constant value of ϵ is not possible any more. But the scaling of energy by the bandwidth ($2Zt$) still remains valid. Also in such cases the symmetry of the DOS is lost because the odd moments of LDOS are functions of $\{\alpha_n\}$ ¹⁴. In our study, the Hamiltonian parameters ϵ and t are obtained from an initial TB-LMTO followed by a massive down-folding to obtain their effective p_z parts⁵⁵.

Fig.4(a) gives the DOS of pristine graphene sheet with hopping parameter $t = -2.544$ and the potential energy term $\epsilon = 0$ (not the calculated value). This is symmetric about the minima, i.e, $E = 0$ and the maxima are at $E = \pm t$. This DOS is similar to those calculated by other methods earlier. Only difference is that we found the peaks at $E = \pm 2.544$ and in those papers they are at $E = \pm 1$ as, in most of the papers the values that they put are $\epsilon = 0$ and $t = 1$.

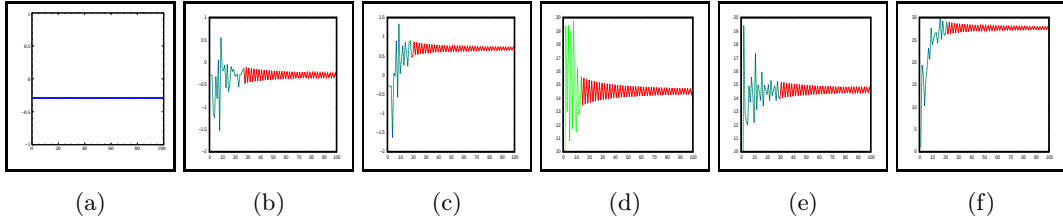


FIG. 3. α 's for Zigzag Nanotubes : (a) pristine ; (b) with single S-W defect ; (c) with double S-W defect. β 's for Zigzag Nanotubes : (d) pristine ; (e) with single S-W defect ; (f) with double S-W defect.

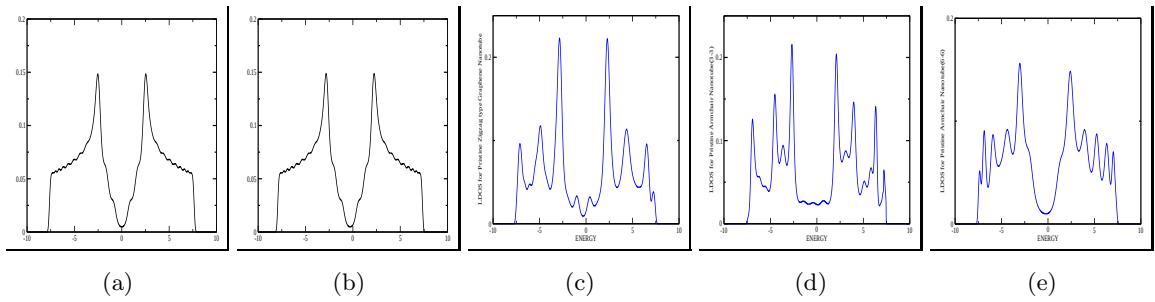


FIG. 4. LDOS for Graphene sheet with (a) $\epsilon = 0, t = -0.2544$ (b) $\epsilon = -0.291, t = -2.544$, LDOS for Single Layer Infinite Pristine Graphene Nanotubes of (c) (6,0) Zigzag type , (d) (3,3) Armchair type , (e) (6,6) Armchair type .

Now, putting the calculated value of $\epsilon = -0.291$ we find Fig 4(b). As expected, the entire graph shifts towards left by an amount $E = 0.291$ and is symmetric about $E = -0.291$.

In Figs.4 the LDOS for pristine nanotube of (a) (6,0) zigzag type , (b) (3,3) armchair types and (c) (6,6) armchair types are shown. There are some geometric distinctions between the infinite flat sheet and the nanotube. Both geometries have no open edges, though, in the tube, this is achieved by periodicity along one edge and shifting other edge to infinity; while for the sheet all edges are shifted to infinity. In spite of these similarities, the LDOS are quite different as seen in Fig.4. As we compare Fig.4(b) with Fig.4(d) and (e), we find LDOS of graphene sheet has more differences with LDOS of (3,3) armchair nanotube as compared to the (6,6) type. This is expected as nanotubes with higher chirality has surface with less curvature, so, has less dissimilarities with infinite sheet.

We can understand this from the recursion

coefficients. In pristine graphene α_n are independent of n and consequently all odd moments of Green's function are zero. This leads to LDOS symmetric about the origin. However to interpret Fig 4(d) and (e) correctly, we compare Fig 3(a) with (b) and (c) ; and note that in the latter α_n oscillates with n while in the former it is a constant. This leads to asymmetric structures in the LDOS for graphene with defects. When topological defects are introduced, the geometrical symmetry is broken, so, the diagonal term of TB-Hamiltonian plays a big role in determining the exact shape of the LDOS. We should like to emphasize this point, so that the general practice of shifting the origin to a $\epsilon = 0$ is discouraged.

LDOS at the point E of zigzag type nanotube with single S-W defect (refer to Fig.5(e)) closely resembles Fig.4(c) with a semiconductor like feature near Fermi energy (E_F). As we enter the defect region, this energy range of low LDOS is filled up with impurity states. This is also true for nanotubes with double S-W defects (refer to

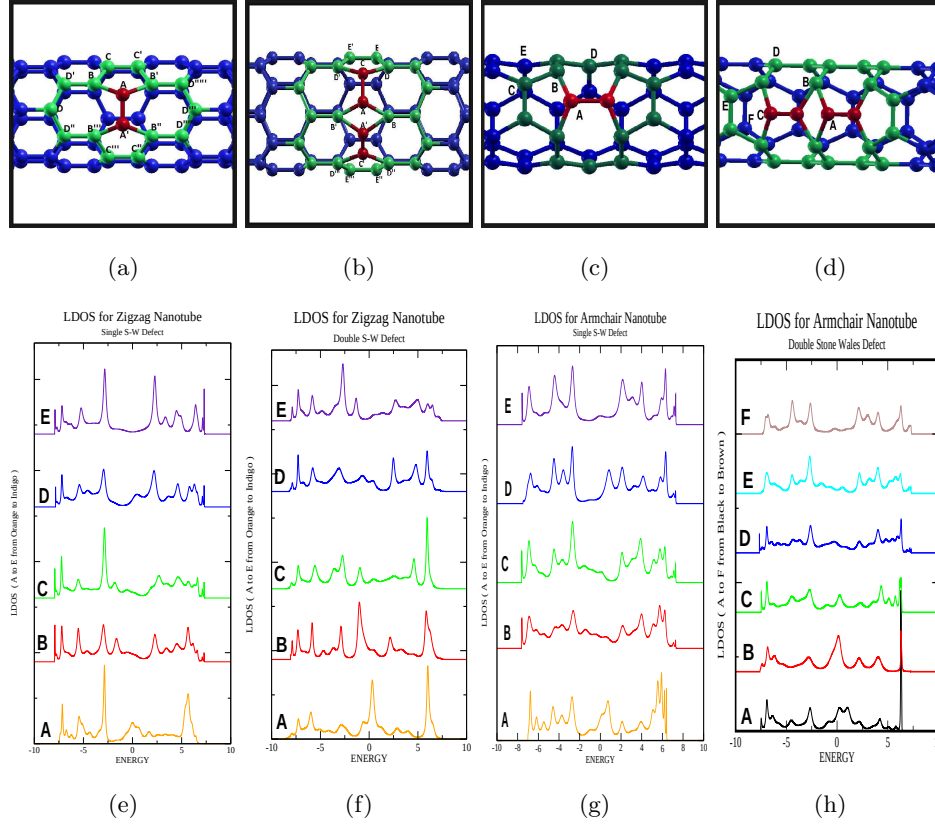


FIG. 5. (Top) The positions at which the LDOS for zigzag(a,b) and armchair(c,d) disordered nanotubes have been calculated ; (bottom) The actual LDOS.

Fig.5(f). In case of armchair nanotube LDOS at E is more metallic in nature (Fig.5(g)). As we get near to the defect, LDOS at E_F increases leading to greater metallicity. The effect of the double S-W defects (refldos(h)) are rather similar except that the metallicity increases further. From this we can surmise that incorporation of S-W defects should increase the metallicity in graphene nanotubes.

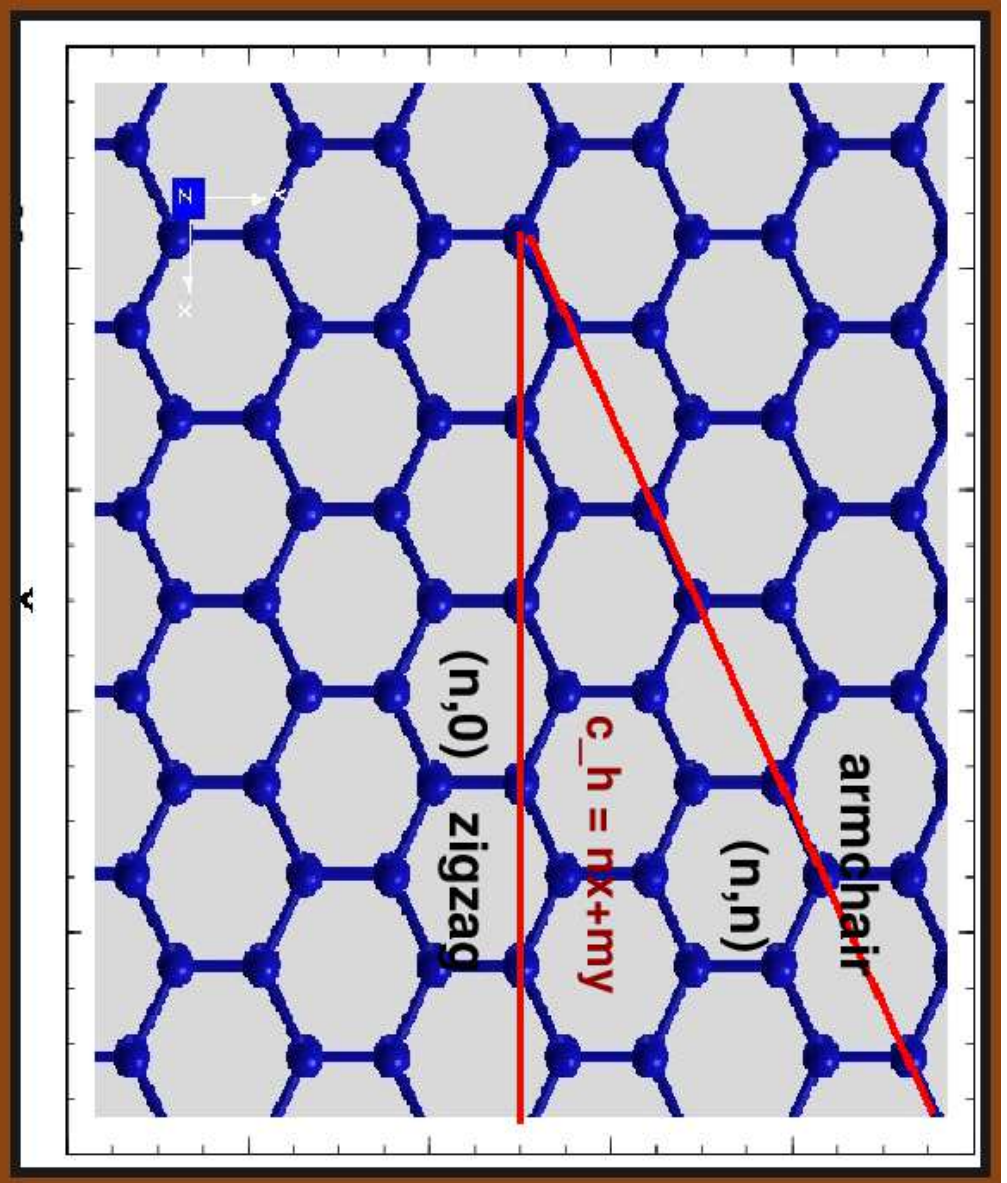
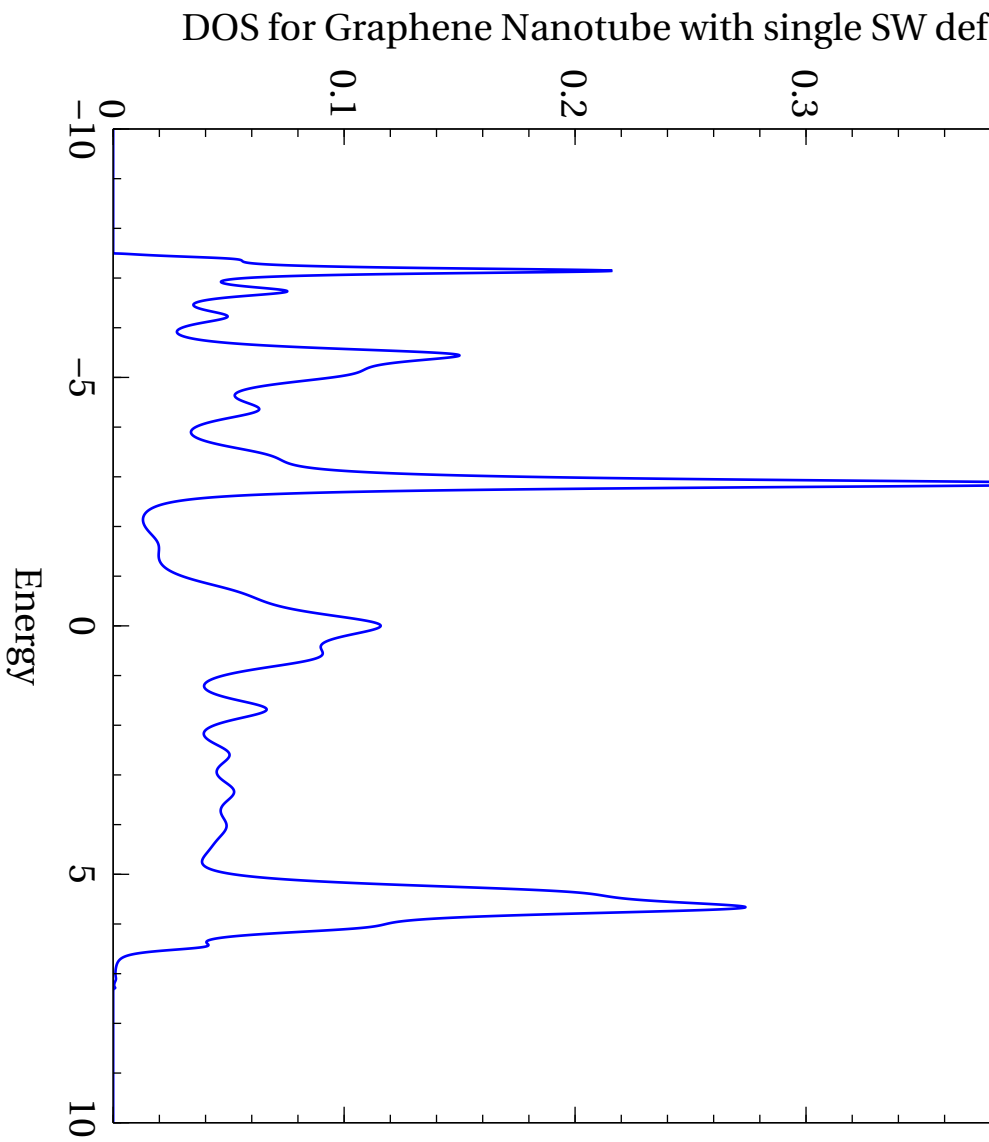
conduction⁵⁷ and magnetism. We propose this unified technique for our future work.

IV. CONCLUSION

We have shown that the recursion method is ideally suited for the study of electronic structure in graphenic materials with extended defects. This method coupled with the TB-LMTO/NMTO provides a first principles description and our application to graphene nanotubes justifies this view. Moreover, the same recursion method, suitably modified can be used to study response functions like resistivity and optical conductivity⁵⁶, phonons and thermal

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